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(54) **PIXEL HAVING AN ORGANIC LIGHT
EMITTING DIODE AND METHOD OF
FABRICATING THE PIXEL**

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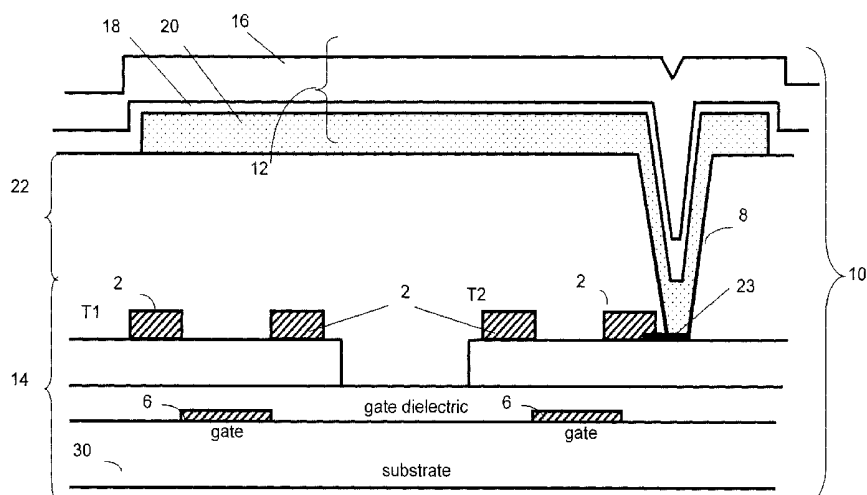
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(57) **ABSTRACT**

A pixel having an organic light emitting diode (OLED) and
method for fabricating the pixel is provided. A planarization
dielectric layer is provided between a thin-film transistor
(TFT) based backplane and OLED layers. A through via
between the TFT backplane and the OLED layers forms a
sidewall angle of less than 90 degrees to the TFT backplane.
The via area and edges of an OLED bottom electrode pattern
may be covered with a dielectric cap.

21 Claims, 13 Drawing Sheets



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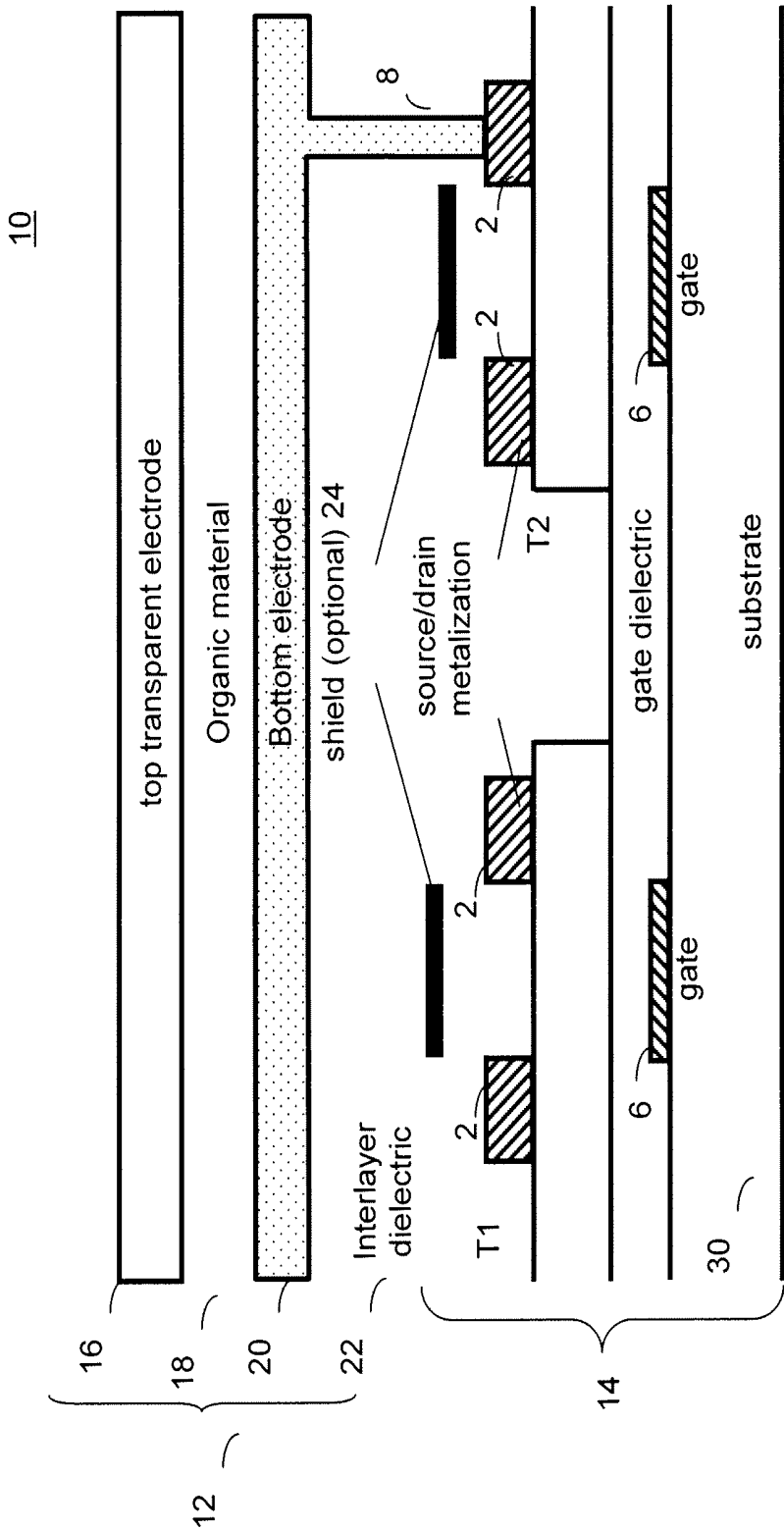


FIGURE 1

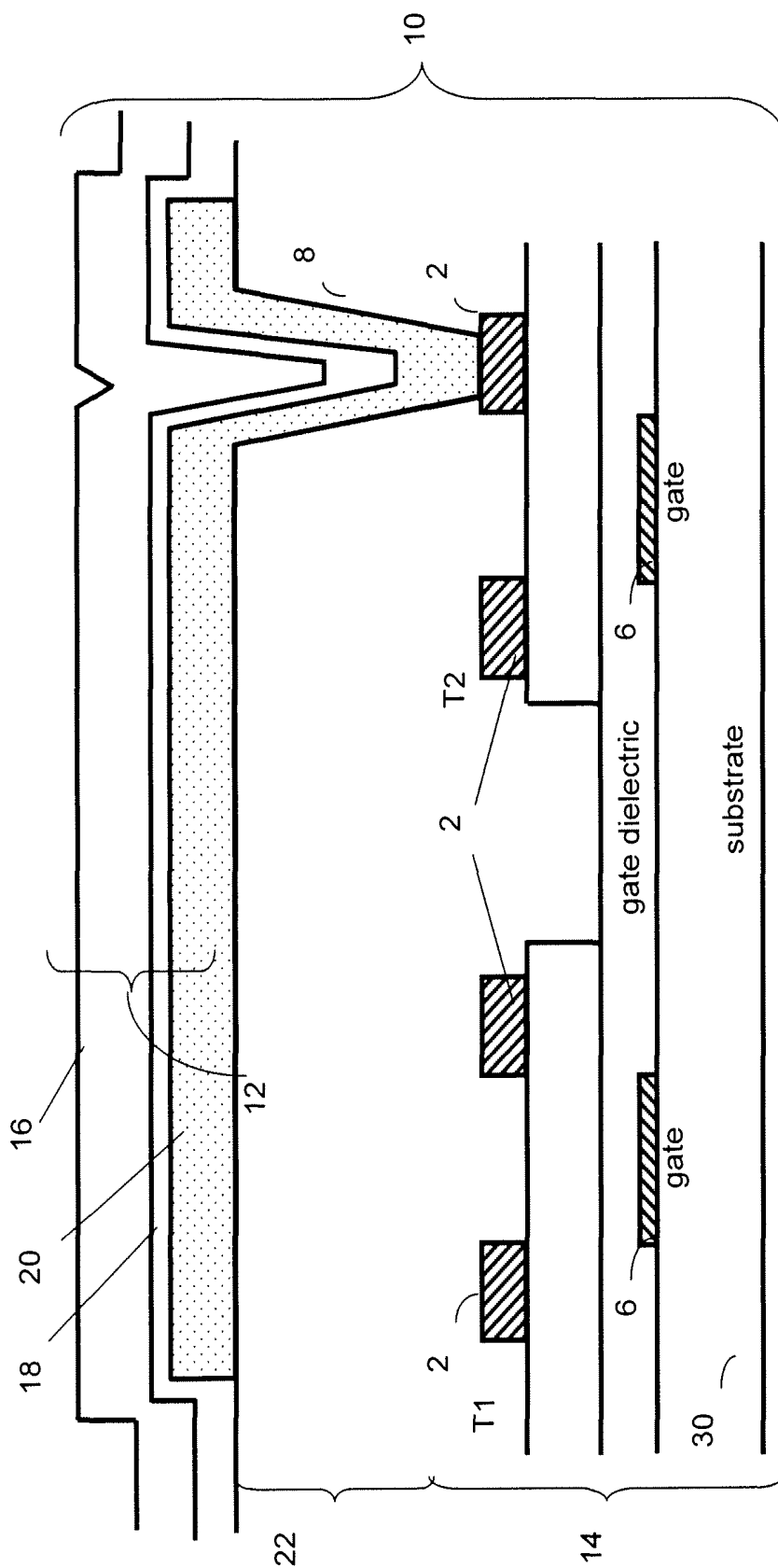


FIGURE 2

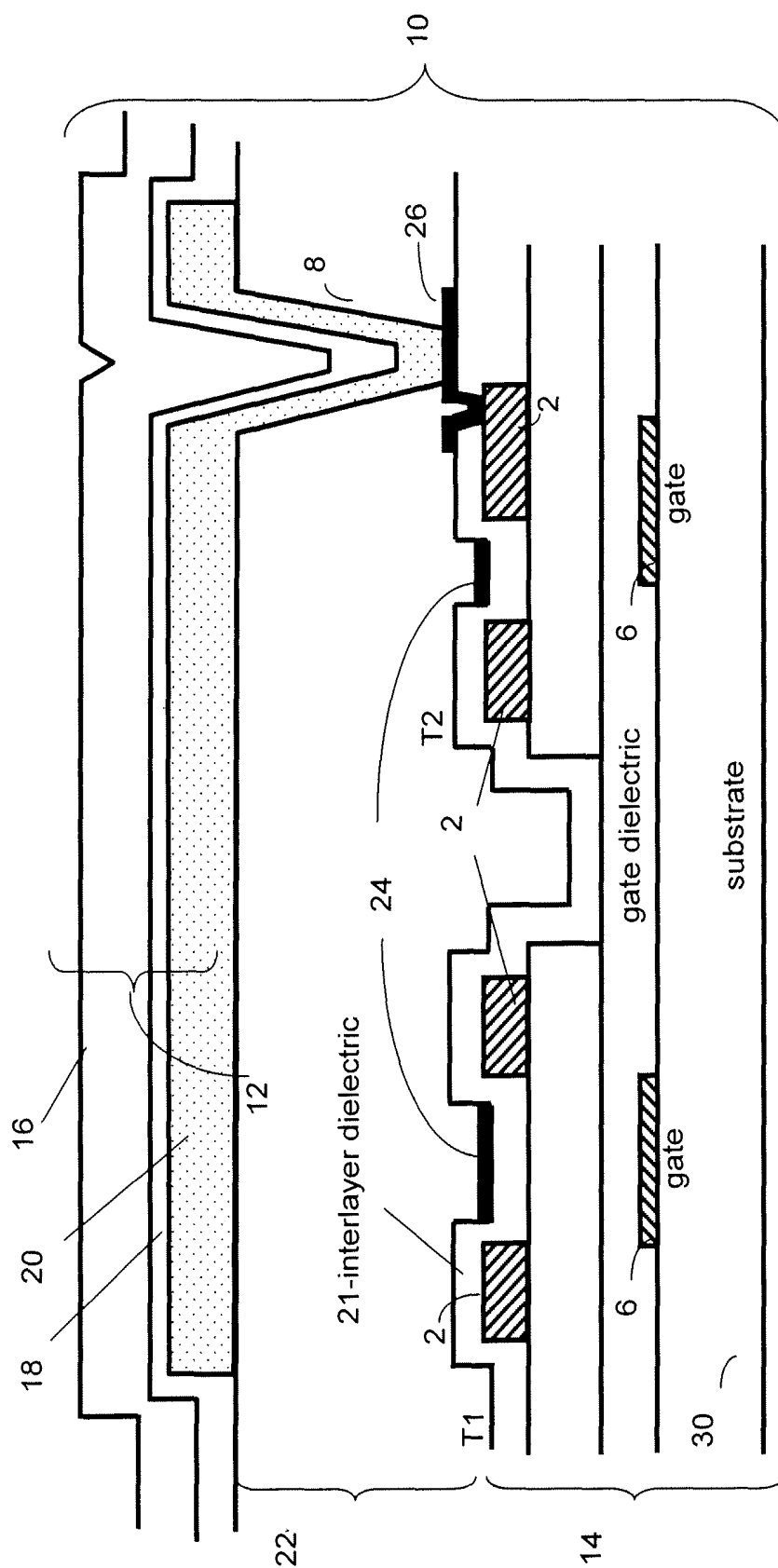


FIGURE 3

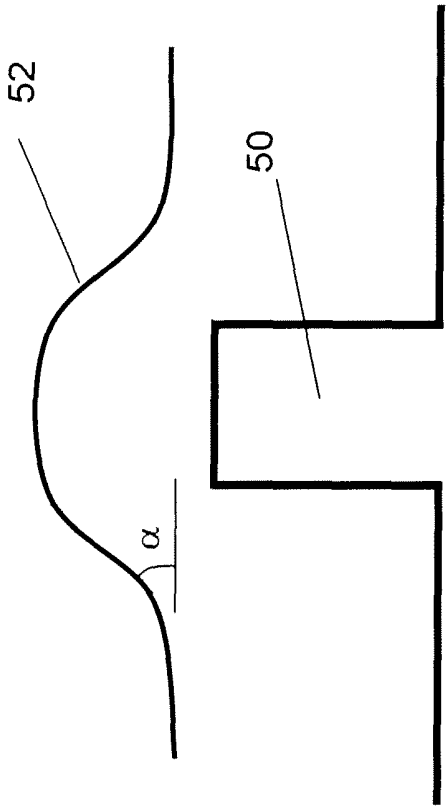


FIGURE 4

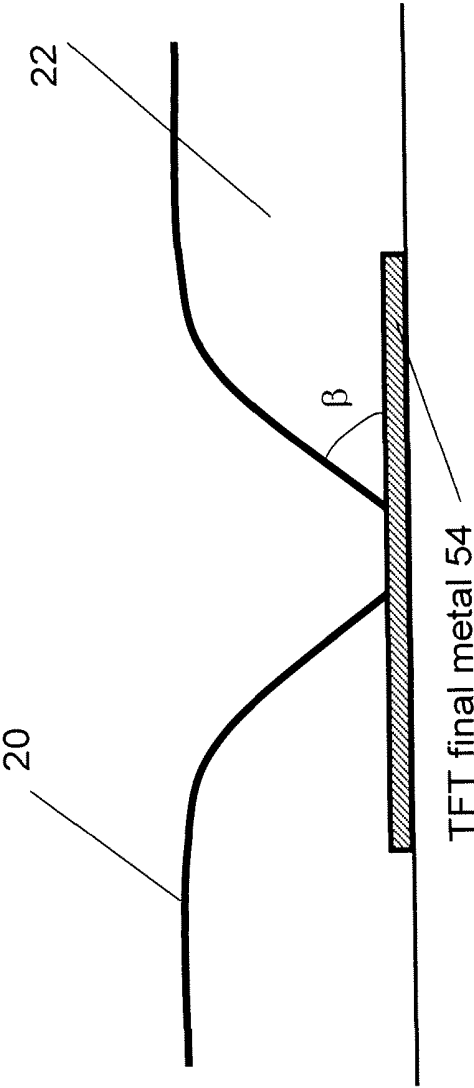


FIGURE 5

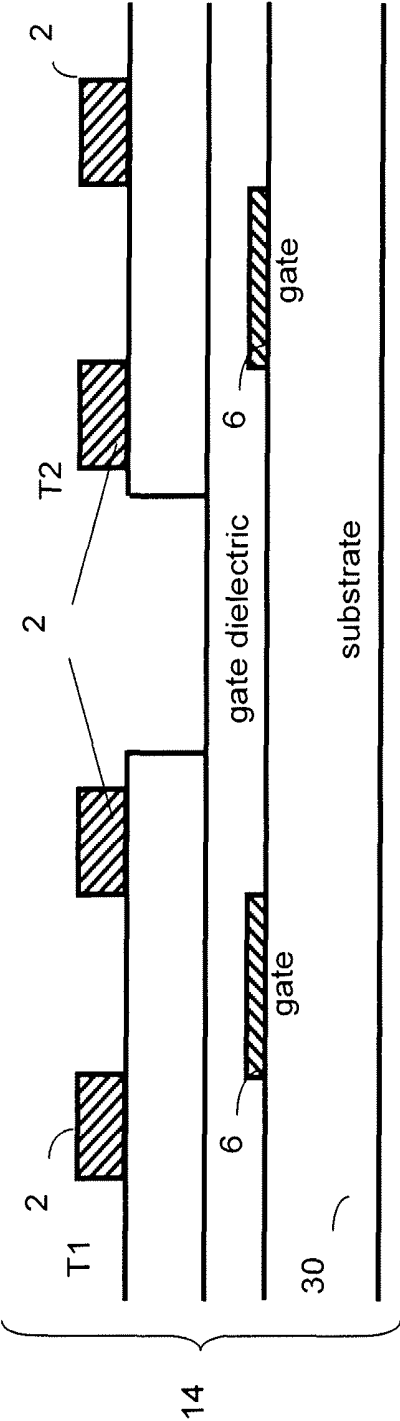


FIGURE 6

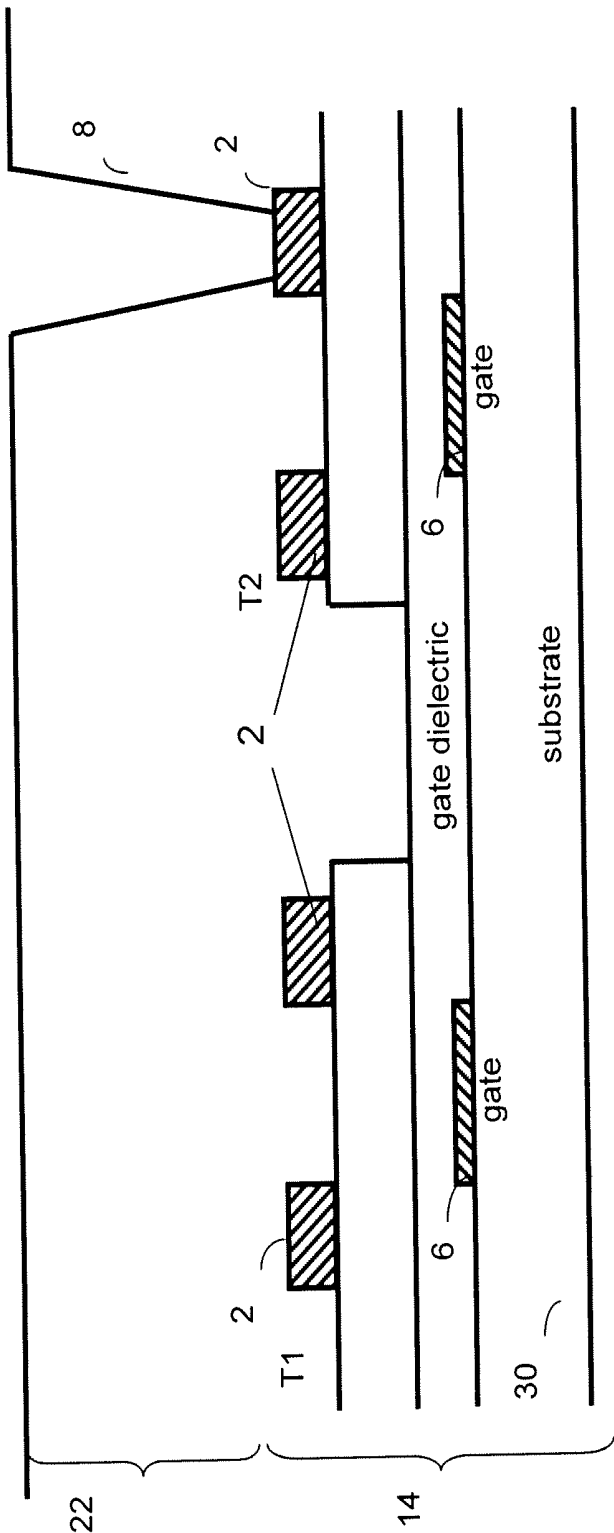


FIGURE 7

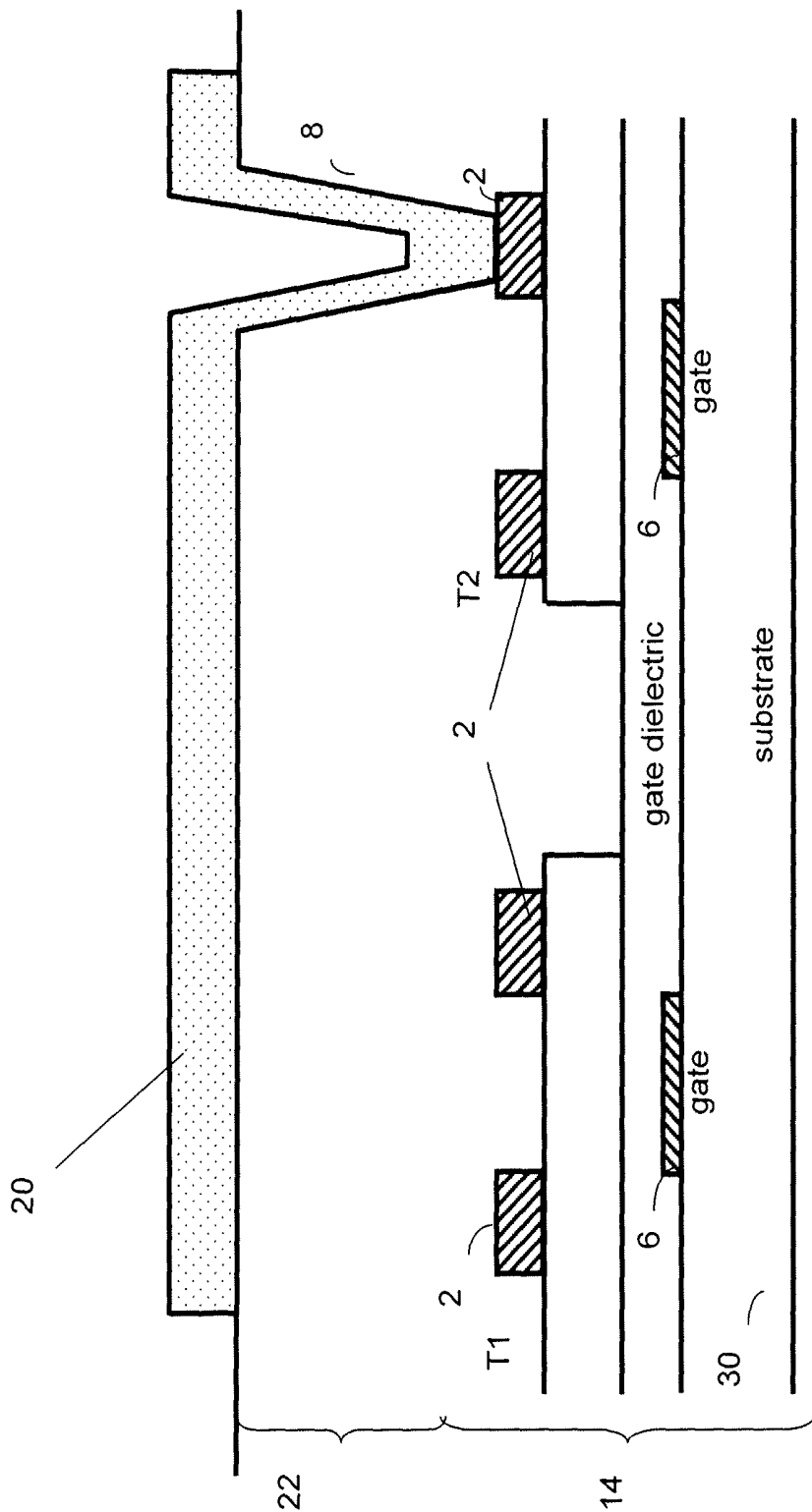


FIGURE 8

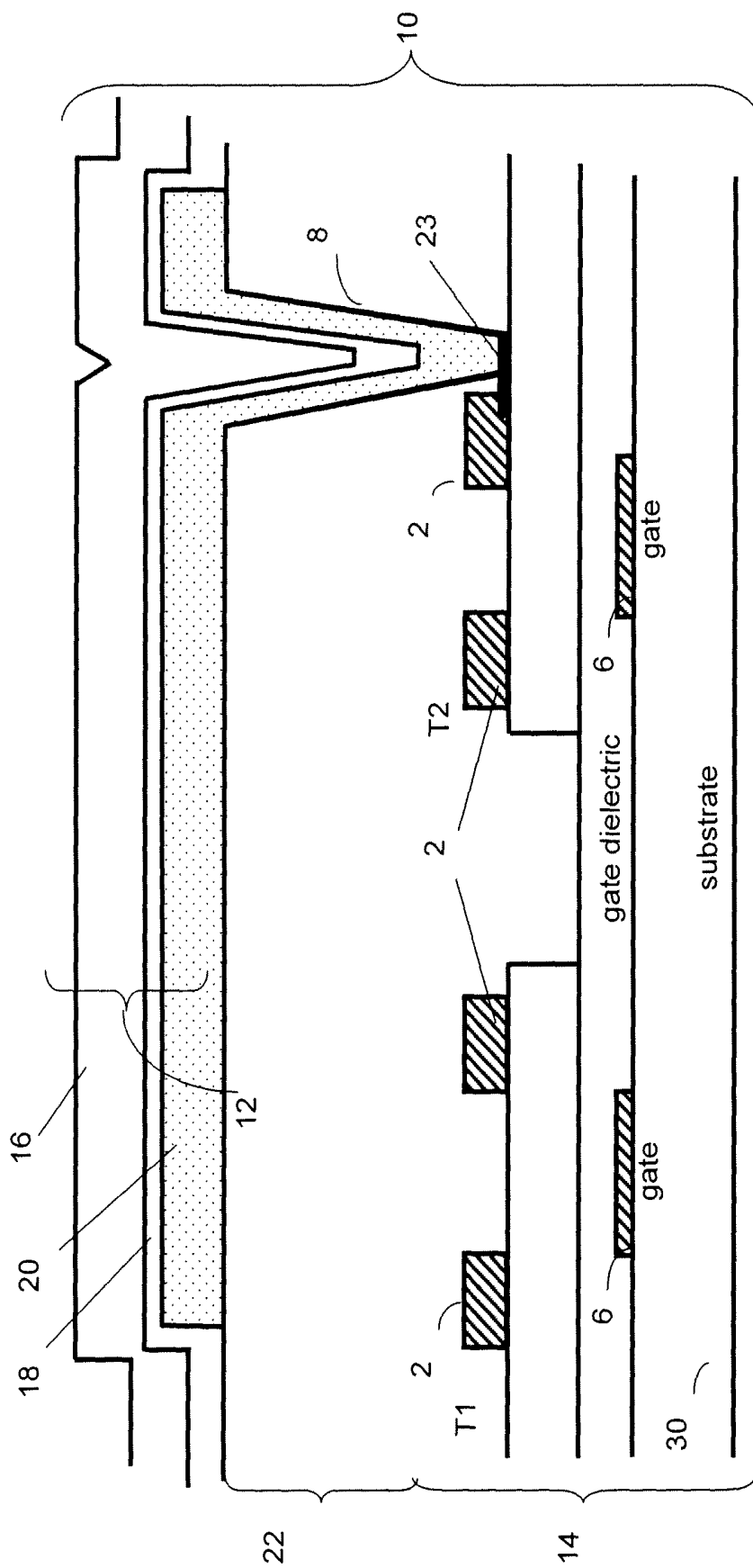


FIGURE 9

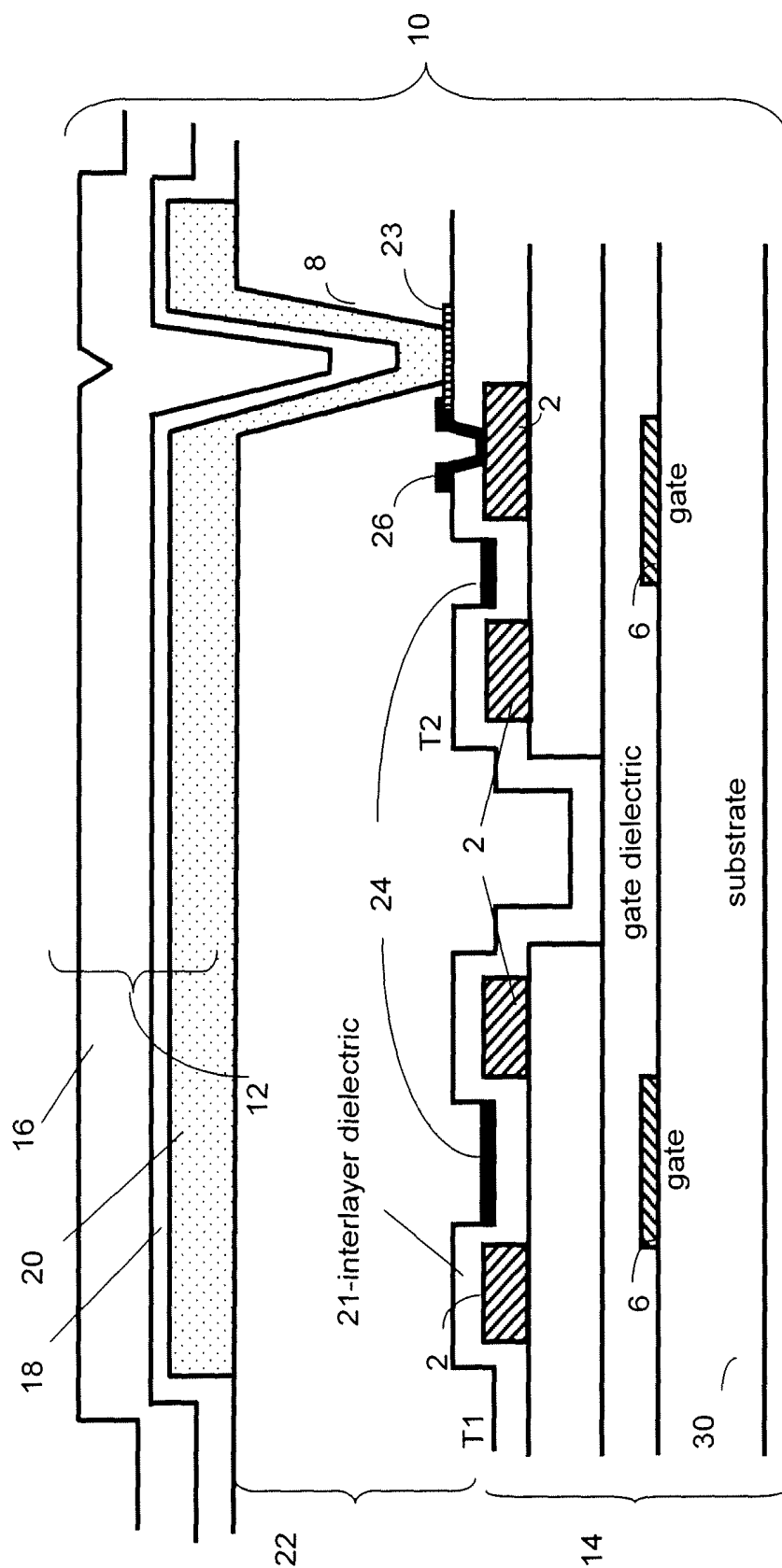


FIGURE 10

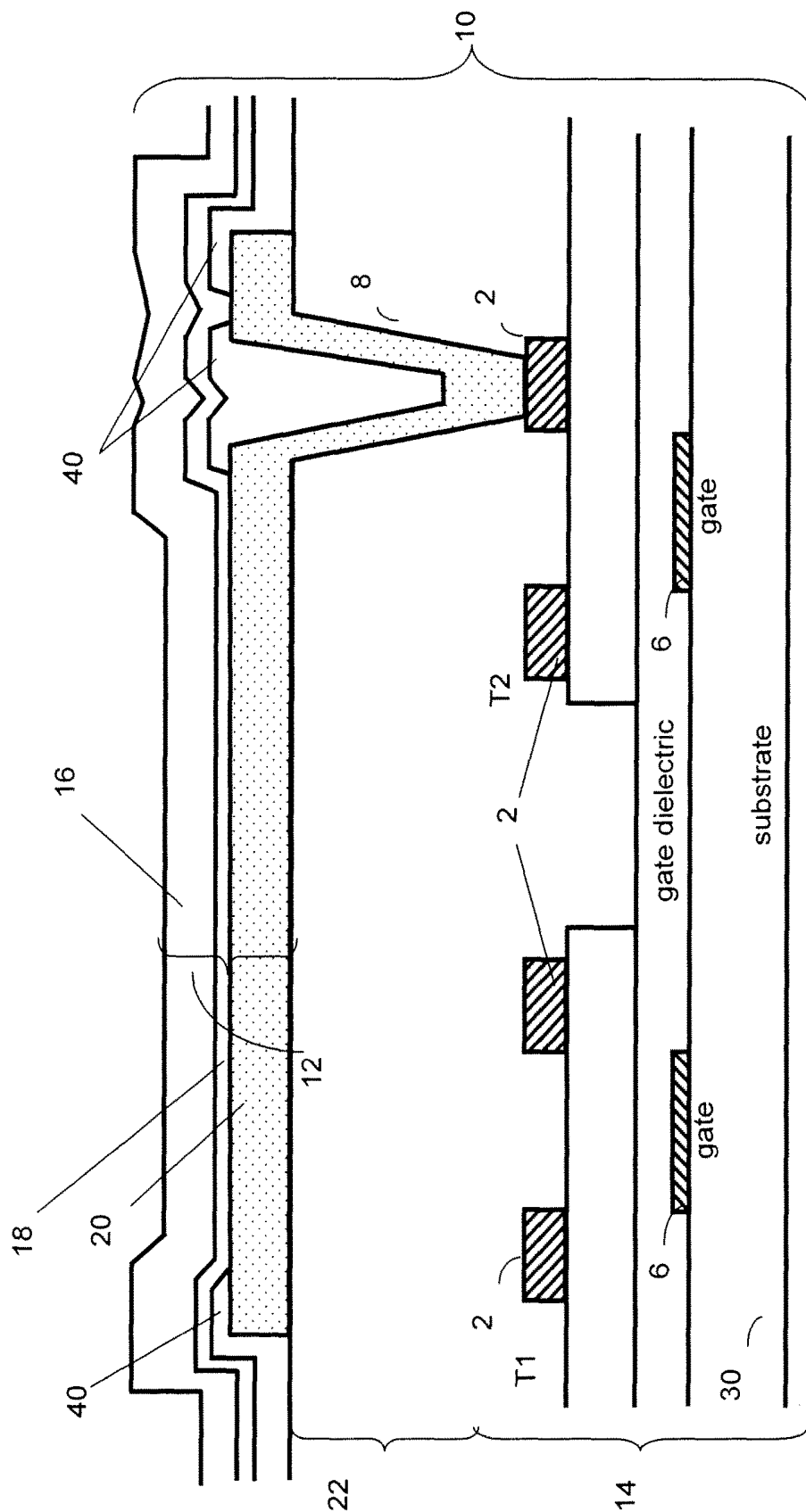


FIGURE 11

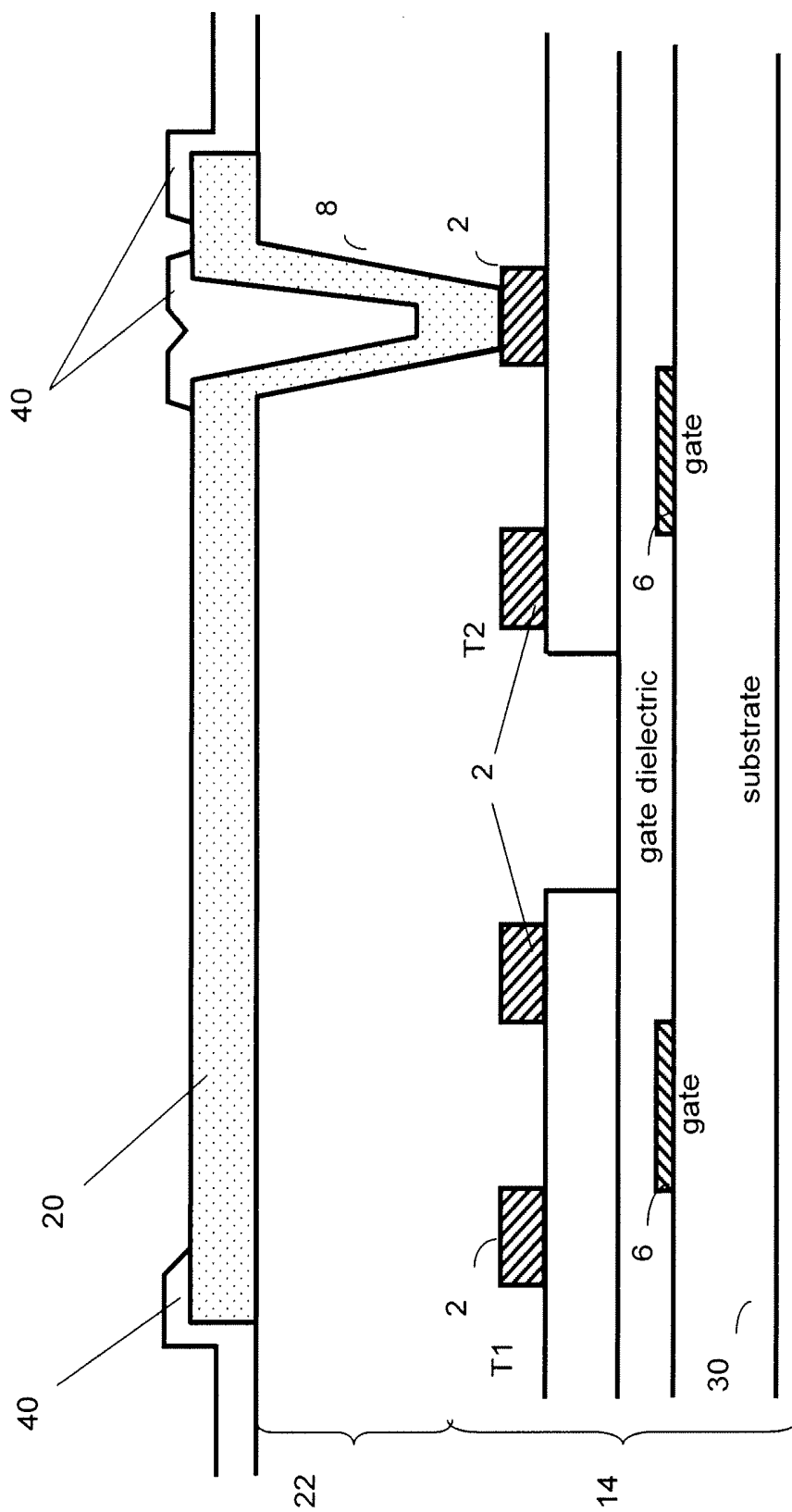


FIGURE 12

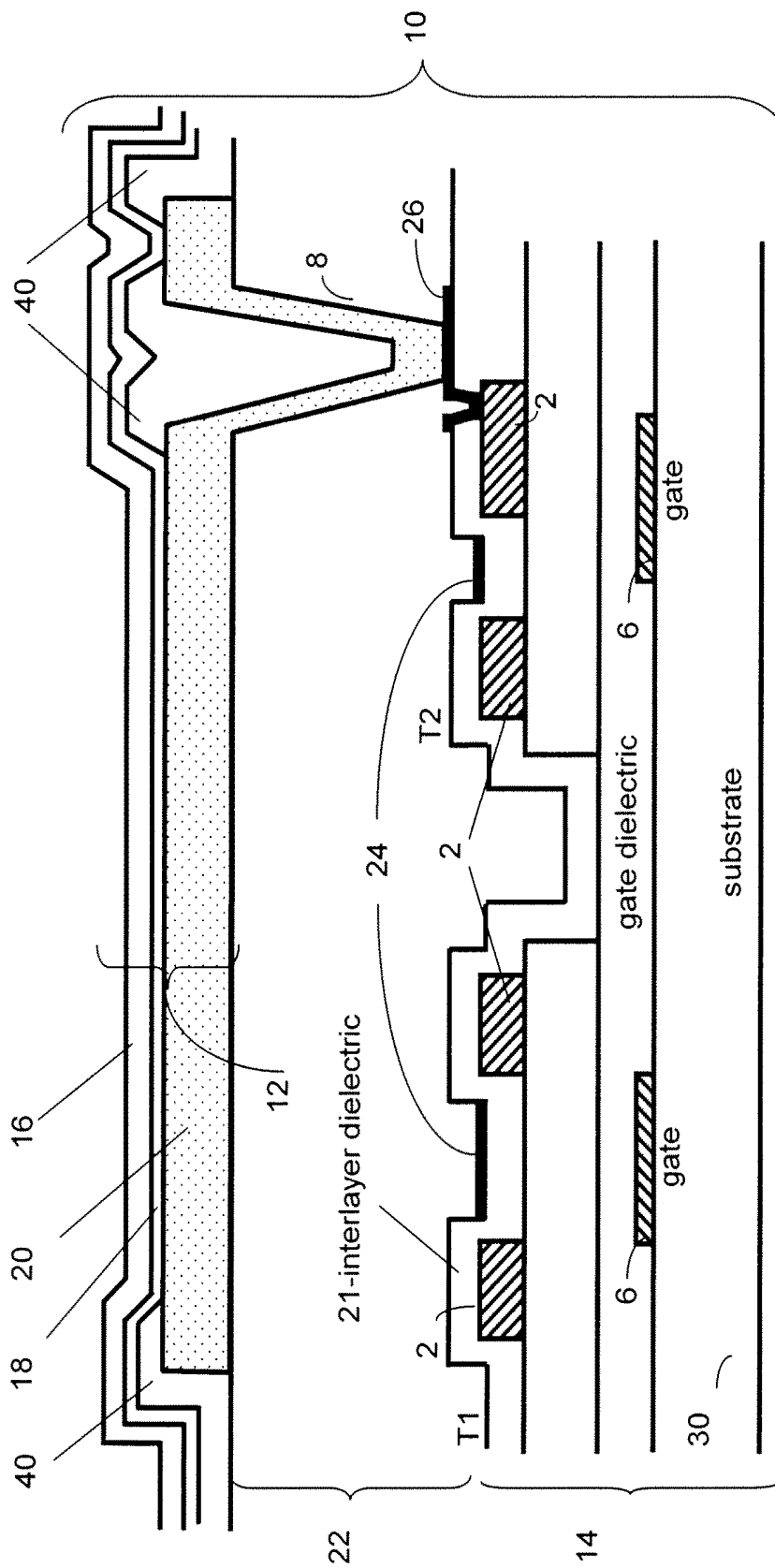


FIGURE 13

1

PIXEL HAVING AN ORGANIC LIGHT EMITTING DIODE AND METHOD OF FABRICATING THE PIXEL

CROSS REFERENCE TO RELATED APPLICATIONS

This application is a continuation of U.S. application Ser. No. 13/112,654, filed May 20, 2011, which is a continuation of U.S. application Ser. No. 10/546,695, filed May 18, 2006, which is a U.S. National Stage of International Application No. PCT/CA2004/00256, filed Feb. 24, 2003, which claims priority to Canadian Patent No. 2,419,704, filed Feb. 24, 2003, each of which is hereby incorporated by reference herein in its entirety.

FIELD OF THE INVENTION

This invention relates to a pixel, more particularly, to a pixel having an organic emitting diode.

BACKGROUND OF THE INVENTION

Organic light emitting diodes (OLEDs) are electro-luminescent (EL) devices for emitting light. The OLED generates light by a current flowing through an organic compound. Pixels including the OLEDs have various advantages, i.e. simple structure, fast response and wide viewing angle. There are two types of matrix displays with the OLEDs, passive type and active type. In the active matrix display, thin-film transistors (TFT) are provided in each pixel to drive the OLEDs of display. The active matrix eliminates high peak driving currents and thereby enables high-resolutions and high information density, improves power consumption and life-time compared to the passive matrix.

Vertical pixel architecture, in which the TFT and the OLED device are stacked vertically, has been developed. Such architecture can achieve higher aperture ratios. This favors using lower mobility amorphous silicon TFT backplanes compared polysilicon TFT technology, which is of higher mobility but also of higher cost.

The difficult part in building the vertical stacked pixels is to make a TFT backplane suitable for subsequent OLED fabrication and provide high yield and good performance of OLED pixels. The OLED device is typically made of very thin layers. Overall thickness of organic layers in the OLED is of the order of 100 nm. For this reason, it requires a smooth substrate to achieve good performance and yield. Step-wise features on the substrate surface and roughness can cause deterioration of light-emitting properties or OLED device failure due to shorts between its electrodes.

It is, therefore, desirable to provide new pixel architecture, which can achieve a high aperture rate, and at the same time, higher yield rate.

SUMMARY OF THE INVENTION

It is an object of the invention to provide novel pixel architecture that obviates or mitigates at least one of the disadvantages of existing pixels.

In accordance with an aspect of the present invention, there is provided vertical pixel architecture in which a planarization dielectric layer is disposed between a TFT based backplane and OLED layers. The planarization dielectric layer is thick enough to smoothen a TFT substrate profile to such an extent that will make it suitable for subsequent

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fabrication of the OLEDs. Preferably, the planarization dielectric and subsequent electrode layer have a roughness of the order of 1 nm to permit successful OLED fabrication.

Electrical connection between TFT circuit and OLED is provided by means through-via made in planarization dielectric.

In accordance with a further aspect of the present invention, there is provided a vertical pixel architecture in which continuous sidewall coverage is provided by pixel electrode material in a through-via profile provided in the planarization dielectric. This is achieved by the formation of sloped sidewalls of the through-via. Preferably, the angle between the via and a TFT substrate is less than 45 degrees.

In accordance with a further aspect of the present invention, the interconnection between TFT final metal and OLED bottom electrode in vertical pixel architecture is provided via a smooth contact plate made of conductive material.

In accordance with a further aspect of the present invention, there is provided a vertical pixel architecture in which a dielectric layer is deposited and patterned on the top of the pixel electrode in such a way that it covers pixel via and the edges of the pixel electrode.

Other aspects and features of the present invention will be readily apparent to those skilled in the art from a review of the following detailed description of preferred embodiments in conjunction with the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

The invention will be further understood from the following description with reference to the drawings in which:

FIG. 1 is a schematic cross-section view showing a vertically integrated pixel in accordance with an embodiment of the present invention.

FIG. 2 is a schematic cross-section view showing an example of the pixel of FIG. 1.

FIG. 3 is a schematic cross-section view showing an example of the pixel of FIG. 1, which incorporates a shield electrode.

FIG. 4 is a schematic diagram showing an example of surface planarization with BCB.

FIG. 5 is a schematic cross-section view showing a sidewall slope of the pixel of FIGS. 2 to 3.

FIGS. 6 to 8 are schematic diagrams showing fabricating process of the pixel of FIG. 2.

FIG. 9 is a schematic cross-section view showing an example of the pixel of FIG. 1, which incorporates a contact plate.

FIG. 10 is a schematic cross-section view showing an example of the pixel of FIG. 1, which incorporates a shield electrode and a contact plate.

FIG. 11 is a schematic cross-section view showing a vertically integrated pixel in accordance with another embodiment of the present invention.

FIG. 12 is a schematic diagram showing fabricating process of the pixel of FIG. 11.

FIG. 13 is a schematic diagram of a vertically integrated pixel in accordance with another embodiment of the present invention.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

A vertically integrated pixel of the present invention is described. FIG. 1 shows a vertically integrated pixel 10 in accordance with an embodiment of the present invention.

The pixel **10** includes OLED device layer **12** and a TFT based backplane **14** (hereinafter referred to as TFT backplane).

The OLED device **12** includes one or more organic layers, a cathode and an anode. In the description, layers between the cathode and the anode are referred to as OLED layers **18**. The OLED layers **18** may be incorporating an electron transport layer, an organic light emitting layer, a hole transport layer, and a hole injection layer. In FIG. 1, an OLED top electrode **16** and an OLED bottom electrode **20** are shown as the cathode and the anode, respectively.

The top electrode **16** is transparent to enable the light to be emitted by the OLED in the direction opposite to the substrate (i.e., top-emitting OLED). However, reverse top-emitting OLED structure, where the bottom electrode **20** is a cathode, and the top electrode **16** is an (transparent) anode, is also possible.

Each pixel of the TFT backplane **14** includes TFT pixel circuits formed on a substrate **30**. In FIG. 1, two TFTs T1 and T2 form a pixel circuit. Each of the transistors T1-T2 has metallization for a source, a drain and a gate **6**. In FIG. 1, "2" represents either a source node or a drain node. However, the pixel **10** may include more than two transistors.

The OLED bottom electrode **20** is formed on the top of the TFT backplane **14**, and is separated from the backplane **14** by a dielectric layer **22**. The dielectric layer **22** is continuously provided everywhere on the top of the TFT pixel circuit except at a through-via **8**, which provides electrical connection between a specific node of the TFT pixel circuit and the OLED bottom electrode **20**. This specific node may be source node or drain node of a TFT, which depends on pixel circuit design and order of deposition for the OLED electrodes and layers. The details of circuit design and OLED fabrication are not to restrict the applicability of the present invention.

Preferably, the planarization dielectric and subsequent electrode layer have a roughness of the order of 1 nm to permit successful OLED fabrication. Optionally, a shield electrode **24** is provided on the top of TFTs.

FIG. 2 shows an example of the pixel **10** of FIG. 1. In FIG. 2, the sidewalls of the through-via **8** are sloped. The OLED bottom electrode material is disposed on the top surface of the dielectric layer **22** and along the sidewall of the sloped through-via **8**.

FIG. 3 is another example of the pixel of FIG. 1. In FIG. 3, the shield electrode **24** is provided above the TFT layers to keep the potential right on the top of the TFT pixel circuit at certain designed level regardless of the potential of the pixel electrode. The shield electrode **24** may be a thin-film conductor, Al, Al-alloy, Mo, Cr or the like. An interlayer dielectric **21** is provided between source/drain and shield layers. The connection between the desired pixel circuit node and the OLED bottom electrode **20** is made by means of a via in the interlayer insulator **21**, an interconnection plate **26** formed in the shield metal layer and the through-via **8** formed in the dielectric layer **22**.

The transistor structure of FIGS. 1-3 is typical for bottom-gate amorphous silicon TFT, and it is shown here as one possible example only. However, the method of pixel integration described here may be applicable in general to any appropriate known TFT backplane, including recrystallized or deposited poly-silicon, micro- and nano-crystalline silicon, CdSe and others.

Active matrix TFT backplane may be fabricated by successive deposition and patterning of metal, insulator and semiconductor layers leading to an overall profile height of the structure that is in the range of a few 100 nm to 1 micron,

with nearly vertical or sharp-angled sidewalls of the structures. On the other hand, in high performance small molecule and polymer organic light emitting devices, active organic layers have an overall thickness in the range of 10-100 nm. This implies that it is desirable to provide the OLED substrate with the roughness in 1 nm range to prevent electrical shorts between OLED layers or top and bottom electrodes. In addition, it is desirable that the substrate is either planar or has sufficiently smooth features whose vertical profile does not prevent reliable step coverage with thin OLED layers and their continuity, where necessary.

In the embodiment of the preset invention, the planarization dielectric and subsequent electrode layer are formed so as to have a roughness of the order of 1 nm. The dielectric layer **22** smoothenes or planarizes the vertical profiles of the structures on the substrate with fabricated TFT **14**. Further, the through-via profile in the dielectric layer **22** enables continuous sidewall coverage by the OLED bottom electrode material, and reduction of thickness of the pixel electrode.

The dielectric layer **22** of the pixel **10** is described in detail. The dielectric layer **22**, which is used for separating the TFT backplane **14** and the OLED bottom electrode **20**, smoothenes or planarizes the vertical profiles of the structures on the substrate **30** with the fabricated TFT backplane **14**. This ensures continuity of the electrodes **16**, **20** and organic layers **18** in the OLED device **12**. This smoothing/planarizing is achieved by using a planarizing dielectric, rather than one coating the substrate conformally. The planarizing dielectric may be an organic polymer such as benzocyclobutene (BCB), polyimide, polyamide, acrylic and others. Minimum thickness of planarization layer required depends on planarization properties of the dielectric and the profile height of TFT backplane. The thickness of planarizing dielectric can be between 0.5 and 5 μm . In the embodiment of the present invention, BCB layer, about 3 micron-thick, produced from photosensitive BCB-material is used as the planarizing layer.

Planarizing dielectric layers are most often produced by application of corresponding initial material or monomer, which can be polymerized on the substrate by means of thermal cure, UV-cure with or without catalyst or by other method. The initial or monomer material can or cannot be patterned by photo-exposure. This property depends on chemical formulation of initial material or monomer by the manufacturer, whether the photosensitive components were added or not. The processing of the former may include steps such as application of initial material, pattern definition by photoexposure through a photomask, pattern developing and final cure. As a result a patterned polymer layer is obtained. The processing of the latter may include application of initial material, cure, application and patterning of the mask, patterning cured polymer by means of plasma or wet etching with the mask, strip the mask. In some cases, like polyimides and BCB, there are available both photosensitive and non-photosensitive versions of initial material that can lead to about the same chemical composition and structure of polymer dielectric material after final cure.

In the embodiment of the present invention, BCB-layer made of photosensitive initial material is used as a planarization dielectric. However, the present invention may be applicable to different types of material, such as but not limited to other planarization materials made of both of photosensitive and non-photosensitive initial formulations.

FIG. 4 shows the planarization effect of BCB-layer. In this example, a TFT substrate is schematically shown as having stepwise profile of the patterns **50** with nearly vertical

sidewalls and profile height of 0.5-0.9 .mu-m before application of BCB. After application of BCB-film, the patterns **50** are translated into 0.3-0.5 micron profiles **52** with the sidewall angle a about 10 degrees on the surface of BCB dielectric. In this example, the BCB-polymer film was produced by spin-coating photosensitive material (photo-sensitive BCB) with subsequent soft bake, exposure, post-exposure bake, pattern developing, solvent removal and cure. The process conditions are shown in Table 1.

TABLE 1

Process conditions for planarization layer		
Nr	Step	Conditions
1	Spin-coating	2500-4000 rpm, 25-40 sec
2	Soft-bake	60-70 degree C., 90 sec
3	Exposure	12-60 sec
4	Post-exposure bake	50-60.degree C., 30 sec
5	Developing	2-4 min
6	Solvent removal	75 degree C., 60 sec
7	Cure	190-250.degree C., 2-4 hrs

The through-via profile in the dielectric **22** of the pixel **10** is now described in detail. The OLED bottom electrode **20** is a conductive material such as indium-tin oxide (ITO) or the like, a metal film, Au, Pd, Ni or the like, sputtered, evaporated or fabricated by other method of thin film deposition. Other metals or thin multi-layer metal coatings may be also applicable. Typically, conductive layers in a flat-panel display substrate are fabricated by sputtering which has limitations in terms of step coverage. On the other hand, the roughness of the conductive layers such as metal films and ITO, increases with layer thickness. A thinner electrode layer produces a smoother surface suitable for OLED fabrication. This also reduces the cost of production. Therefore, a reduction of the thickness of the pixel electrode while maintaining its continuity over substrate profile is desirable.

If the through-via had a nearly vertical sidewall, the thickness of the metal to cover sidewall continuously, could be of the same order as the depth of the via, which is equal to the thickness of the planarization dielectric layer (in a range of few micron). In the pixel **10** of FIGS. 2 to 3, the sidewall is made sloped rather than vertical. That permits the thickness of the pixel electrode to be reduced substantially in a vertically stacked pixel structure.

FIG. 5 shows one example of a sidewall slop inside the via **8** of FIGS. 2 and 3. In FIG. 5, an angle .beta. between the OLED bottom electrode **20** on the sidewall and a TFT final material **54** is less than 90 degrees. If planarizing polymer dielectric is formed from photosensitive initial formulation, the sloped sidewall can be achieved by means of appropriate exposure conditions.

An example of sidewall slope control in the through-via for BCB-layer (i.e., dielectric **22**), which is produced from photosensitive initial material, is presented in Table 2.

TABLE 2

Sidewall angle in cured BCB layer which was produced from photosensitive BCB-material as a function of exposure time	
Exposure time, sec	Sidewall angle, deg
20	45
30	33
13	27

The formation of the layer and patterning of the vias were achieved by means of spin-coating photosensitive BCB material with subsequent soft-bake, light-exposure, developing, developer solvent removal and cure. In Table 1, the sidewall angle .beta. between the planarization layer **22** and the TFT final material **54** is shown as a function of photo-sensitive BCB-exposure time.

After the exposure, the film underwent **30** seconds post-exposure bake at **55**. degree C. and was developed for around 3 minutes in the developer solvent followed by 60 second bake at 75. degree C. for developer solvent removal and then final cure.

The conditions for spin-coating, soft-bake, exposure, post-exposure bake and final cure are variable, and may depend on pixel design requirements. Recommendations about process conditions of Photo-BCB are given, for example, by "Cyclotene™ 4000 Series Advanced Electronic Resins (Photo-BCB)" of Dow Chemical™, at <http://www.dow.com/cyclotene/prods/402235.htm>.

As shown in Table 2, the sidewall angle .beta. relates to the exposure time. The sidewall angle .beta. becomes smaller when exposure time is longer. For example, for the sidewall angle .beta. of less than 45 degrees and the planarization dielectric thickness of around 3 .mu.m, the continuous coverage of the via sidewalls was achieved with a pixel electrode thickness of order 100 nm. This is much less than the through-via depth and enables the electrode surface of the OLED bottom electrode **20** to be sufficiently smooth.

For polymer dielectric material made of non-photosensitive initial formulation, the sloped sidewall can be also achieved. For example, this can be done, by optimizing masking and plasma etching steps.

The parameters, materials and/or process of fabricating the sloped through-vias **8** are adjusted so as to: ensure the continuous sidewall coverage by a material of the pixel electrode; make the roughness of the OLED electrode small enough (1 nm order) to prevent electrical shorts between the OLED top electrode **16** and the OLED bottom electrode **20**.

One example of fabricating the pixel **10** of FIG. 2 is shown in FIGS. 6 to 8. First, the TFT backplane **14** is fabricated (FIG. 6) on the substrate **30**. Next, the TFT backplane **14** is coated with a planarization layer **22**, where the vias **8** with sloped sidewalls are opened to the selected nodes of the TFT backplane **14** (FIG. 7). For BCB planarization layer made of photosensitive formulation, BCB material is applied by spin coating, and processed including soft-bake, UV-exposure through a photomask, post-exposure cure, developing, solvent removal and final cure. This sequence gives patterned material (with the through-vias **8**) whose layer thickness and via sidewall slope depend on processing conditions, such as the exposure time as described above. Typically, surface roughness of cured BCB-layer is about 1 nm. Then, a thin residual layer on the bottom of the through-vias **8** is removed by plasma etching. Etching conditions are optimized for short etching time and minimum roughening of the BCB surface. For example, the fabrication of the pixel **10** may include plasma etching in CF4+O2 gas mixture or SF6+O2 gas mixture, a combination of high power high density plasma (for example, inductively coupled plasma) and low power reactive ion etching to achieve short etching time (few-20 seconds); and virtually no change in roughness after plasma etching.

Subsequently, a conductive material is deposited and patterned to form the OLED bottom electrode **20** (FIG. 8). Finally; the OLED layers **18** and transparent electrode top electrode **16** of the OLED are continuously applied over the pixels (FIG. 2).

The shield electrode **24** of FIG. **3** is now described in detail. As shown in FIG. **3**, optional shield electrode can be incorporated in a pixel structure. After formation of the TFT backplane **14**, interlayer dielectric **21** is deposited. This can be done by means of CVD, plasma-enhanced CVD process or other method. Silicon nitride, silicon oxide or silicon oxide nitride with the thickness between 0.1 and 1 μm can be used as the interlayer dielectric **21**. After formation of the vias in the interlayer dielectric that provide interconnection between source-drain and shield metallization layers, shield metal layer is deposited and patterned to form the shield electrodes **24** and interconnection plates **26**. The interconnection plates **26** serve to carry the potential from the certain node of TFT pixel, which can be either source or drain of a TFT, to the bottom electrode of OLED device **20**. Then, the planarization layer **22** is applied and patterned, as described above, which is followed by deposition and patterning of OLED bottom electrode **20**, deposition of the OLED layers **18** and top transparent electrode **16**.

FIG. **9** shows another example of the pixel of FIG. **1**. In FIG. **9**, TFT source/drain metal overlaps a contact plate **23** made of thin and smooth conductive material, such as Cr, Mo or other. The contact plate **23** is formed by deposition and patterning of conductive films on the flat portion of pixel area. Preferably, the thickness of the contact plate **23** is between 50 and 150 nm.

The contact between the certain node of the TFT circuit, which is in the source/drain metallization layer of the TFT backplane **14**, and the OLED bottom electrode **20** is made via the contact plate **23** rather than directly.

Depending on structure and fabrication method of the TFT backplane **14**, the source-drain metal may have surface roughness well in excess of 1 nm. This may be the case if relatively thick metal layer, especially Al or Al-alloy, is used for source/drain metallization. Such a source-drain metallization can be required for the reasons associated with particular TFT fabrication process or display design. For example, highly conductive routing metallization is beneficial for reduction of power dissipation or better OLED brightness uniformity over the substrate area, especially if the display size is large. If such a source/drain metal would be in a direct contact with the bottom electrode of the OLED **20**, its surface roughness is translated into the roughness of electrode **20** inside via area. This can make this area a source of shortages between OLED electrodes **20** and **16** and therefore cause OLED failure. Thus, in the pixel of FIG. **9**, the contact to the bottom OLED electrode **20** is made via the smooth contact plate **23** formed in separate layer. In addition, if the TFT final metal (source/drain-metal) **2** is Al or Al-alloy or the like, and the bottom OLED electrode **20** is conductive oxide such as ITO, having a contact to the electrode **20** made of Cr, Mo or the like instead of Al/Al-alloy will reduce contact resistance, heat dissipation in the contact and improve overall contact reliability.

The contact plate **23** is formed before source/drain metallization of the TFT backplane **14**. The TFT source drain-metal, which is formed next, has to overlap some portion of the contact plate **23** but leave a sufficient portion open for formation of via **8**. In addition, it is desirable that source/drain metal can be selectively etched over contact plate metal. For example, if source/drain metal is Al or Al-alloy, using Cr for contact plate would provide excellent wet-etch selectivity. Roughness of the order 1 nm is easy to achieve with thin layers of metals such as Cr, Mo, Ti produced by sputtering, evaporation or other methods. Appropriate thin multi-layer metal coating can off cause be also used for contact plate **23**.

After the TFT backplane **14** with the contact plate **23** is formed, further steps, application and patterning of the planarization dielectric layer **22**, deposition and patterning of the bottom OLED electrode **20**, deposition of the OLED layers **18** and OLED top electrode are performed in a manner described above.

FIG. **10** shows another example of the pixel of FIG. **1**. In FIG. **10**, the pixel has the shield electrode **24** and the contact plate **23**. As described above, the shield **24** is formed to keep electric potential on the top of the TFTs at certain desired level. As the TFT backplane **14** is formed, the interlayer dielectric **21** is deposited. Then the contact plate **23** is formed of a thin and smooth metal layer such as Cr, Mo or the like on a flat portion of the pixel area. Preferably, the thickness of the contact plate **23** is between 50 and 150 nm. The vias in the dielectric **21** are patterned to provide interconnections between the source/drain and shield metallization levels where necessary. Then, shield metal is deposited and patterned to form the shield electrodes **24** and the interconnection plates **26**. The interconnection plate **26** is to overlap the contact plate **23** but to leave its sufficient portion open, as shown schematically in FIG. **10**. Preferably, the shield metal is selectively etched over the contact plate metal. As the TFT backplane **14** with the shield electrodes **24** and the contact plates **23** is formed, the planarization dielectric **22** is applied and through-via **8** is formed on the top of the portion of contact plate **23**, which is free from shield metal (FIG. **10**). Further steps (deposition and patterning of the bottom OLED electrode **20**, deposition of the OLED layers **18** and OLED top electrode) may be performed in a similar manner as described above.

FIG. **11** shows a vertically integrated TFT-OLED pixel in accordance with another embodiment of the present invention. The dielectric layer **22** and the through-via profile of FIG. **11** are similar to those of FIG. **2**.

The pixel **10** of FIG. **11** further includes an additional dielectric layer, i.e., dielectric cap **40**, which is deposited on the top of the OLED bottom electrode **20**. The dielectric cap **40** is patterned so as to cover the via area and the edges of the OLED bottom electrode pattern leaving the rest of the OLED bottom electrode **20** uncovered. The OLED layers **18** and the top electrode **16** are deposited in a similar manner as described above.

The dielectric cap **40** is provided to avoid breakage of continuously deposited OLED top electrode layers at the pixel edges, and therefore to prevent shortage of OLED devices. Further, the dielectric cap **40** insulates the via area, which, depending on the structure and fabrication method of the TFT backplane **14**, may have higher surface roughness than the rest of the OLED bottom electrode **20** and may be therefore a source of the shortage of the OLED device.

The dielectric cap **40** is made of material, which may be either polymer dielectric (such as, BCB, polyimide, other polymer dielectric) or inorganic insulator (such as, silicon oxide, silicon nitride, silicon oxide-nitride).

The thickness of the polymer insulator may be from a few 100 nm to a few micron. With the polymer insulator, as shown above, the sidewall profile of the cap pattern can be made smooth enough to enable continuous coverage with the OLED layers **18** and OLED top electrode **16**.

With inorganic insulator, the thickness of the dielectric cap **40** is adjusted in such a way to enable continuous coverage of the profile steps associated with the cap layer by the OLED top electrode **16**. The thickness of an inorganic insulator can be between 50 and 500 nm (most preferably 50 to 200 nm). In addition, the conditions of dry or wet

patterning of an inorganic insulator, such as silicon oxide or the like, can be adjusted to form the sloped sidewalls.

One example of the fabricating process for the pixel 10 of FIG. 11 is seen from FIGS. 6 to 8, 11 and 12. As the TFT backplane 14 is formed on the substrate 30 (FIG. 6), the planarization dielectric 22 is applied where the vias 8 with sloped sidewalls are opened to the source-drain metal 2 (FIG. 7). A conductive material is deposited and patterned to form the OLED bottom electrode 20 (FIG. 8). Then, the dielectric cap 40 is disposed as described above (FIG. 12). Then, the OLED layers 18 and the electrode are disposed and which completes the formation of the pixel structure shown in FIG. 11.

FIG. 13 shows a vertically integrated pixel in accordance with another embodiment of the present invention. The pixel 10 in FIG. 13 includes the shield electrode 26 and the dielectric cap 40. First, the TFT backplane 14 is fabricated followed by deposition and patterning of the interlayer dielectric 21 and the shield electrode 24. The vias in the interlayer dielectric are formed to provide interconnection between the source/drain and interconnection plates 26 made in the shield metallization layer, where necessary. Next, shield metal is deposited and patterned to form the shield electrodes 24 and the interconnection plates 26. Next, the planarization dielectric 22 and the OLED bottom electrode 20 are deposited and patterned in a similar manner as described above. Then, the cap dielectric layer 40 is disposed and pattern as described in the previous embodiment. Finally, the OLED layers 18 and the OLED top electrode 16 are formed.

According to the embodiments of the present invention, the vertical pixel integration provides higher aperture ratio, which leads to: the possibility of using more advanced multi-transistor pixel driver circuit for improved display performance without taking up extra light-emitting area from the pixel; the possibility of using a TFT backplane, such as amorphous silicon, having lower mobility in contrast to poly-silicon, thereby simplifying the manufacturing process and reducing cost; and the reduction of current density through OLED providing higher operational stability and improved lifetime of the display device.

Further, the fabrication process sequences and critical processing details described above solve a variety of issues pertinent to vertical integration such as: smoothening out/planarizing vertical profiles in the dielectric layer 22 of the structures on the TFT substrate 14 to enable continuity of the OLED device layers 12; continuous sidewall coverage by pixel electrode material in the through-via profile in the dielectric 22; roughness of the order of 1 nm on the dielectric 22 and subsequent electrode layer, which enables successful OLED fabrication and to higher yield rate; and capping structure feature which do not comply to OLED fabrication process in terms of step height, sidewall angle and surface roughness by a dielectric layer. The via and edges of the electrode are covered with the dielectric cap 40.

While particular embodiments of the present invention have been shown and described, changes and modifications may be made to such embodiments without departing from the true scope of the invention which is defined in the claims. What is claimed is:

1. A pixel having a vertical architecture, comprising:
 - an organic light emitting diode (OLED) device having a bottom electrode, one or more OLED layers and a transparent top electrode for emitting light;
 - a thin-film transistor (TFT) based backplane for electrically driving the OLED device, the TFT based backplane being vertically integrated with the OLED layers

and located below said bottom electrode to form a top-emitting OLED, the TFT based backplane comprising:

source and drain nodes; and

a thin conductive contact plate formed entirely on a flat portion of the pixel area and electrically coupled to a source or drain node, the thin conductive contact plate defined by a top surface, a bottom surface, and side surfaces, its vertical dimension defined by the top and bottom surfaces substantially smaller than its horizontal dimensions defined by the side surfaces; a planarization dielectric layer provided between the TFT based backplane and the OLED bottom electrode so as to planarize the vertical profile on the TFT based backplane, said planarization dielectric layer being in direct contact with both said TFT based backplane and said OLED bottom electrode;

a via in said planarization dielectric layer to provide a communication path between said TFT based backplane and said OLED device and through said thin conductive contact plate; and

a dielectric layer deposited on top of said bottom electrode and covering said via and all the edges of said bottom electrode while leaving the rest of said bottom electrode uncovered.

2. The pixel as claimed in claim 1, wherein the sidewall of said via in the planarization layer is sloped against the TFT based backplane.

3. The pixel as claimed in claim 2, wherein the TFT based backplane includes:

a substrate;

an interlayer dielectric layer on the source and drain nodes; and

an interconnection plate patterned on a via of the interlayer dielectric layer and being connected to the source or drain node and the thin conductive contact plate; wherein the planarization dielectric layer planarizes the vertical profile on the substrate with the fabricated TFT based backplane, and the sloped via providing the communication path through the interconnection plate.

4. The pixel as claimed in claim 3, wherein the thin conductive contact plate is formed on a flat portion of the interlayer dielectric layer such that the interconnection plate overlaps a part of the contact plate.

5. The pixel as claimed in claim 3, further comprising a shield electrode disposed between the planarization dielectric layer and the interlayer dielectric layer, which is located separately from the interconnection plate.

6. The pixel as claimed in claim 2, wherein the TFT based backplane includes:

a substrate;

wherein the thin conductive contact plate is formed such that the source or drain material overlaps the thin conductive contact plate and the planarization dielectric layer planarizes the vertical profile on the substrate with the fabricated TFT based backplane.

7. The pixel as claimed in claim 6, further comprising a shield electrode formed separately from said thin conductive contact plate.

8. The pixel as claimed in claim 1, in which said dielectric layer is patterned in such a way that it insulates the OLED layers from the OLED bottom electrode at pixel edges and in and around the via while leaving the rest of the OLED bottom electrode in the direct contact with the OLED layers.

9. The pixel as claimed in claim 8, wherein said dielectric layer includes polymer dielectric or inorganic insulator.

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10. The pixel as claimed in claim 8, wherein said dielectric layer includes material selected from the group from BCB, polyimide, polymer dielectric, silicon nitride and a thin film inorganic.

11. The pixel as claimed in claim 1, wherein the pixel has a roughness of the order of 1 nm on the planarization dielectric layer and subsequent electrode layer.

12. The pixel as claimed in claim 1, further comprising continuous sidewall coverage by pixel electrode material in the via profile in the planarization dielectric layer.

13. The pixel as claimed in claim 1, further comprising a shield electrode formed over the TFT.

14. The pixel as claimed in claim 1, wherein the planarization dielectric layer includes photosensitive benzocyclobutene (BCB), the slope of the via being adjusted by the exposure time of the photosensitive BCB.

15. A method of fabricating a pixel, the pixel having an organic light emitting diode (OLED) bottom electrode, one or more OLED layers on the OLED bottom electrode, a transparent top electrode, and a thin-film transistor (TFT) based backplane for electrically driving the OLED and including a substrate, the method comprising the steps of:
 providing the TFT based backplane on said substrate, including forming within the TFT based backplane a thin conductive contact plate entirely on a flat portion of the pixel area and electrically coupled to a source or drain node of the TFT based backplane, the thin conductive contact plate defined by a top surface, a bottom surface, and side surfaces, its vertical dimension defined by the top and bottom surfaces substantially smaller than its horizontal dimensions defined by the side surfaces;
 providing a dielectric layer on the TFT based backplane, including the step of planarizing a vertical profile in the dielectric layer so as to planarize the vertical profile on the substrate with the TFT based backplane, said planarized dielectric layer being in direct contact with said TFT based backplane;
 forming a via in said planarization dielectric layer to provide a communication path between said TFT based backplane and said OLED device and through said thin conductive contact plate;
 depositing said OLED bottom electrode directly on top of said planarized dielectric layer and extending through said via into direct contact with said thin conductive contact plate of said TFT based backplane; and
 depositing a dielectric layer on top of said bottom electrode and covering said via and all the edges of said bottom electrode while leaving the rest of said bottom electrode uncovered.

16. A method as claimed in claim 15, wherein forming said via which provides the communication path between the TFT backplane and the OLED device through the planarization dielectric layer, comprises forming the via such that the sidewall of the via in the planarization layer is sloped against the TFT based backplane.

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17. A method as claimed in claim 15, wherein providing said dielectric layer between the OLED bottom electrode and the OLED layers, comprises patterning the dielectric layer in such a way that it insulates the OLED layers from the OLED bottom electrode at pixel edges and in and around the via while leaving the rest of the OLED bottom electrode in the direct contact with the OLED layers.

18. A method as claimed in claim 15, wherein the planarization dielectric layer including photosensitive benzocyclobutene (BCB), further comprising the step of adjusting the exposure time of the photosensitive BCB such that the sidewall of the via in the planarization layer is sloped against the TFT based backplane.

19. A method as claimed in claim 15, wherein the pixel is formed such that the pixel has a roughness of the order of 1 nm on the planarization dielectric layer and subsequent electrode layer.

20. A method as claimed in claim 15, further comprising the step of providing continuous sidewall coverage by pixel electrode material in the via profile in the planarization dielectric layer.

21. A method of fabricating a pixel, the pixel having an organic light emitting diode (OLED) bottom electrode, one or more OLED layers on the OLED bottom electrode, and a thin-film transistor (TFT) based backplane for electrically driving the OLED and including a substrate, the method comprising the steps of:

providing the TFT based backplane on said substrate, including forming within the TFT based backplane a thin conductive contact plate entirely on a flat portion of the pixel area and electrically coupled to a source or drain node of the TFT based backplane, the thin conductive contact plate defined by a top surface, a bottom surface, and side surfaces, its vertical dimension defined by the top and bottom surfaces substantially smaller than its horizontal dimensions defined by the side surfaces;

providing a dielectric layer on the TFT based backplane, including the step of planarizing a vertical profile in the dielectric layer so as to planarize the vertical profile on the substrate with the TFT based backplane, said planarized dielectric layer being in direct contact with said TFT based backplane;

forming a via in said planarization dielectric layer to provide a communication path between said TFT based backplane and said OLED device and through said thin conductive contact plate;

depositing said OLED bottom electrode directly on top of said planarized dielectric layer and extending through said via into direct contact with said thin conductive contact plate of said TFT based backplane, and

depositing a dielectric layer on top of said bottom electrode and covering said via and all the edges of said bottom electrode while leaving the rest of said bottom electrode uncovered.

* * * * *

专利名称(译)	具有有机发光二极管的像素和制造像素的方法		
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摘要(译)

提供了一种具有有机发光二极管 (OLED) 的像素和制造该像素的方法。在基于薄膜晶体管 (TFT) 的背板和OLED层之间提供平坦化介电层。TFT背板和OLED层之间的通孔形成与TFT背板小于90度的侧壁角。OLED底部电极图案的通孔区域和边缘可以用介电帽覆盖。

